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6/12/03 (NE)
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants	: Trung T. Doan and Gurtej S. Sandhu	Attorney Docket No.	: 500300.02
Serial No.	: 10/054,692	Group Art Unit	: 3725
Filed	: December 19, 2001	Examiner	: William Hong
Title	: POLISHING PAD REFURBISHER FOR IN SITU, REAL-TIME CONDITIONING AND CLEANING OF A POLISHING PAD USED IN CHEMICAL-MECHANICAL POLISHING OF MICROELECTRONIC SUBSTRATES		

Mail Stop Non-Fee Amendment
Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT

Sir:

Please amend the above-captioned patent application as follows:

In the Specification:

Please replace the paragraph beginning on column 2, line 18, with the following rewritten paragraph:

--CMP processes must also consistently and accurately produce a uniform, planar surface on the wafer because it is important to accurately focus the image of circuit patterns on the surface of the wafer. As the density of integrated circuits increases, it is often necessary to accurately focus the critical dimensions of the circuit pattern to better than a tolerance of approximately 0.1 μm. Focusing the circuit patterns to such small tolerances, however, is very difficult when the distance between the emission source and the surface of the wafer varies

because the surface of the wafer is not uniformly planar. In fact, several devices may be defective on a wafer with a non-uniformly planar surface. Thus, CMP processes must create a highly uniform, planar surface.--